

NGTB25N120SWG

IGBT - Inverter Welding

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for welding applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 10 μs Short Circuit Capability
- These are Pb-Free Devices

Typical Applications

- Welding

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	1200	V
Collector current @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	I_C	50 25	A
Pulsed collector current, T_{pulse} limited by T_{Jmax}	I_{CM}	100	A
Diode forward current @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	I_F	50 25	A
Diode pulsed current, T_{pulse} limited by T_{Jmax}	I_{FM}	100	A
Gate-emitter voltage Transient gate-emitter voltage ($T_{pulse} = 5 \mu s$, $D < 0.10$)	V_{GE}	± 20 ± 30	V
Power Dissipation @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	P_D	385 192	W
Short Circuit Withstand Time $V_{GE} = 15 V$, $V_{CE} = 500 V$, $T_J \leq 150^{\circ}C$	T_{SC}	10	μs
Operating junction temperature range	T_J	-55 to $+175$	$^{\circ}C$
Storage temperature range	T_{stg}	-55 to $+175$	$^{\circ}C$
Lead temperature for soldering, 1/8" from case for 5 seconds	T_{SLD}	260	$^{\circ}C$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



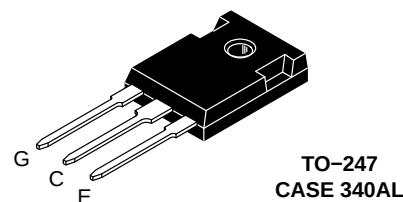
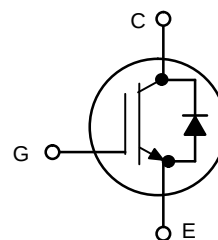
ON Semiconductor®

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25 A, 1200 V

$V_{CEsat} = 2.0 V$

$E_{off} = 0.60 mJ$



MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB25N120SWG	TO-247 (Pb-Free)	30 Units / Rail

NGTB25N120SWG

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.39	$^{\circ}\text{C/W}$
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	0.63	$^{\circ}\text{C/W}$
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 500\text{ }\mu\text{A}$	$V_{(BR)CES}$	1200	–	–	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 25\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 25\text{ A}, T_J = 175^{\circ}\text{C}$	V_{CEsat}	– –	2.00 2.40	2.40 –	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 400\text{ }\mu\text{A}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 175^{\circ}\text{C}$	I_{CES}	– –	– –	0.4 2	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	–	–	200	nA

Input capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}	–	4420	–	pF
Output capacitance		C_{oes}	–	151	–	
Reverse transfer capacitance		C_{res}	–	81	–	
Gate charge total	$V_{CE} = 600\text{ V}, I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	Q_g	–	178	–	nC
Gate to emitter charge		Q_{ge}	–	39	–	
Gate to collector charge		Q_{gc}	–	83	–	

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-on delay time	$T_J = 25^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 25\text{ A}$ $R_g = 10\text{ }\Omega$ $V_{GE} = 0\text{ V/ }15\text{ V}$	$t_{d(on)}$	–	87	–	ns
Rise time		t_r	–	74	–	
Turn-off delay time		$t_{d(off)}$	–	179	–	
Fall time		t_f	–	136	–	
Turn-on switching loss		E_{on}	–	1.95	–	mJ
Turn-off switching loss		E_{off}	–	0.60	–	
Total switching loss		E_{ts}	–	2.55	–	
Turn-on delay time	$T_J = 150^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 25\text{ A}$ $R_g = 10\text{ }\Omega$ $V_{GE} = 0\text{ V/ }15\text{ V}$	$t_{d(on)}$	–	84	–	ns
Rise time		t_r	–	94	–	
Turn-off delay time		$t_{d(off)}$	–	185	–	
Fall time		t_f	–	245	–	
Turn-on switching loss		E_{on}	–	2.39	–	mJ
Turn-off switching loss		E_{off}	–	1.26	–	
Total switching loss		E_{ts}	–	3.65	–	

DIODE CHARACTERISTIC

Forward voltage	$V_{GE} = 0\text{ V}, I_F = 25\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 50\text{ A}, T_J = 175^{\circ}\text{C}$	V_F	– –	2.10 2.30	2.60 –	V
Reverse recovery time	$T_J = 25^{\circ}\text{C}$ $I_F = 25\text{ A}, V_R = 400\text{ V}$ $di_F/dt = 200\text{ A/}\mu\text{s}$	t_{rr}	–	154	–	ns
Reverse recovery charge		Q_{rr}	–	1.3	–	μC
Reverse recovery current		I_{rrm}	–	15	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

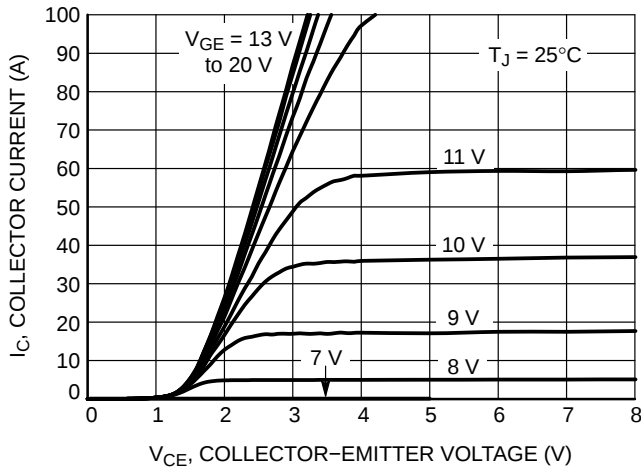


Figure 1. Output Characteristics

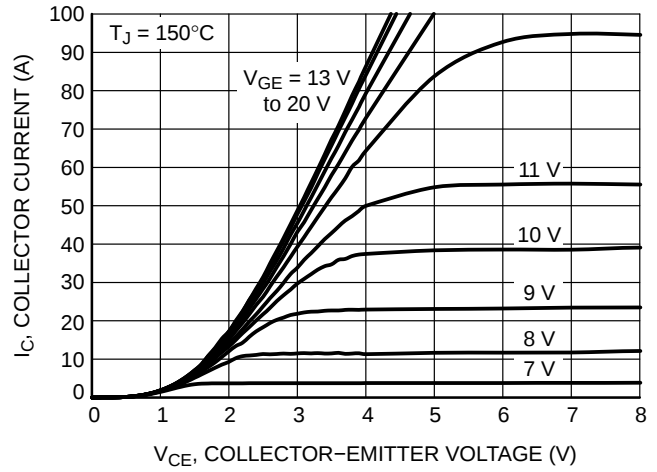


Figure 2. Output Characteristics

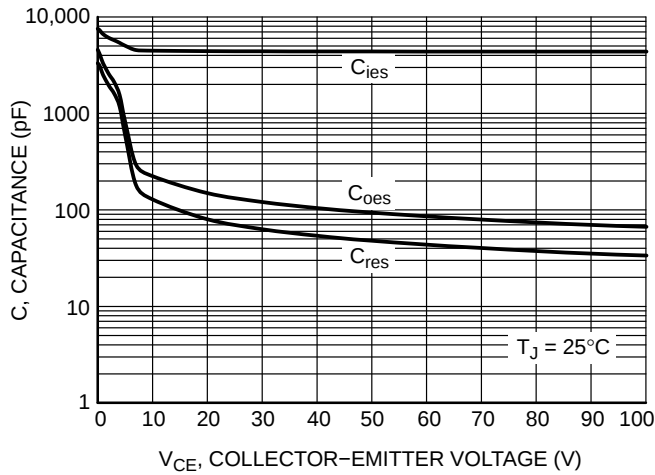


Figure 3. Typical Capacitance

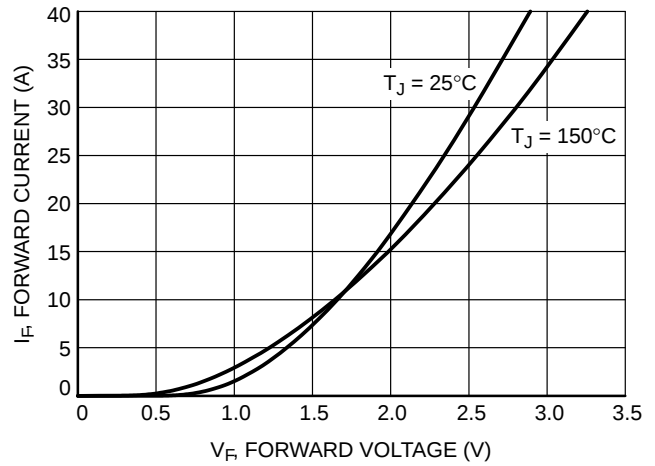


Figure 4. Diode Forward Characteristics

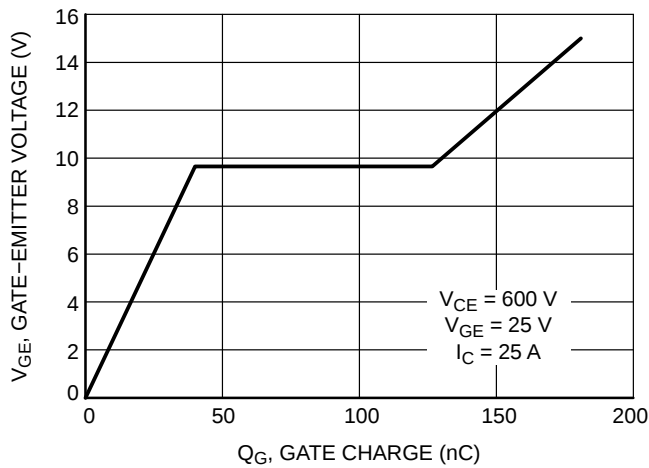


Figure 5. Typical Gate Charge

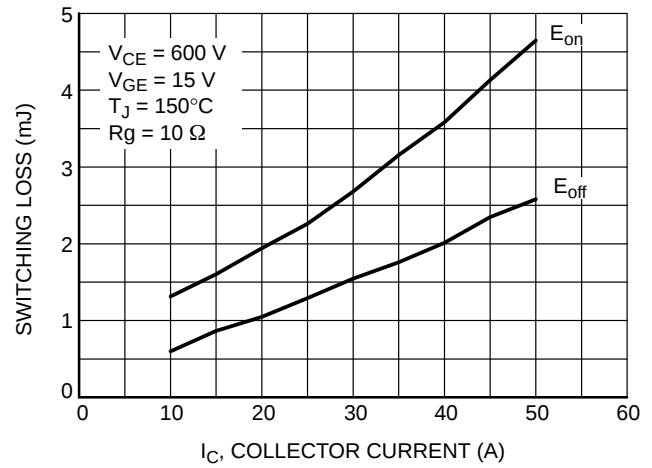


Figure 6. Switching Loss vs. I_C

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TYPICAL CHARACTERISTICS

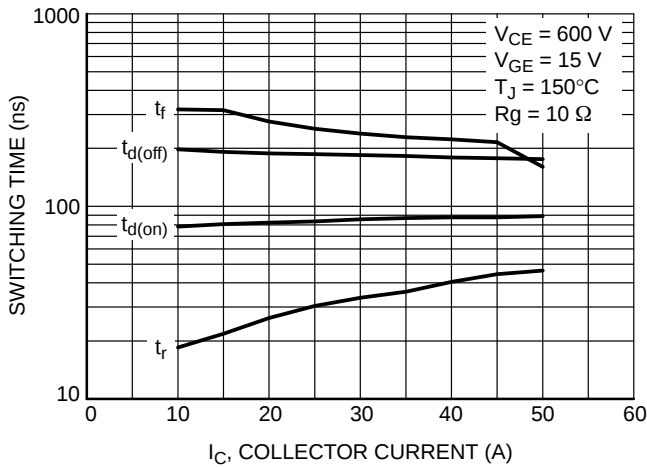


Figure 7. Switching Time vs. I_C

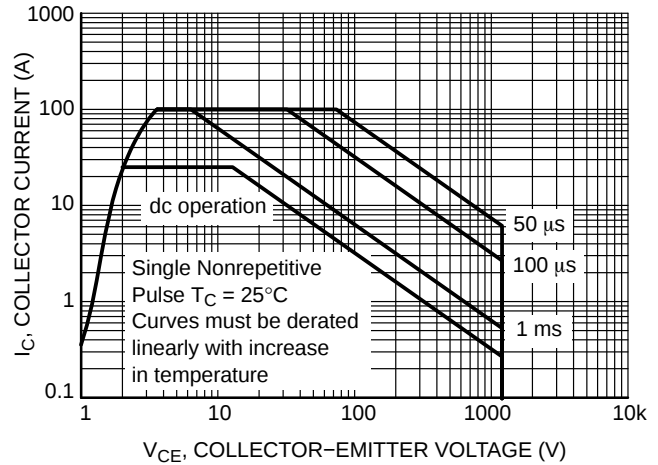


Figure 8. Safe Operating Area

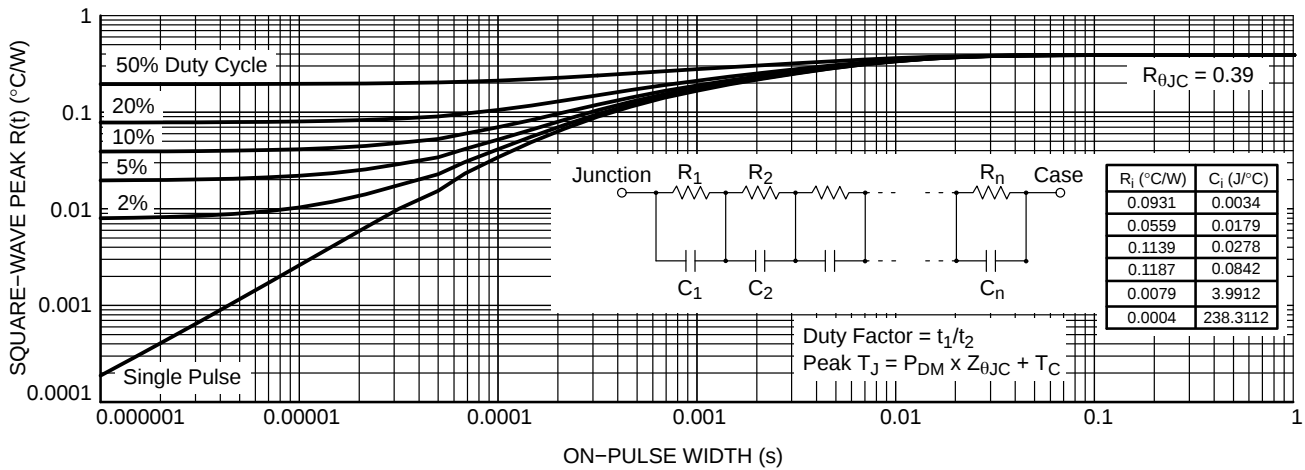


Figure 9. IGBT Die Self-heating Square-wave Duty Cycle Transient Thermal Response

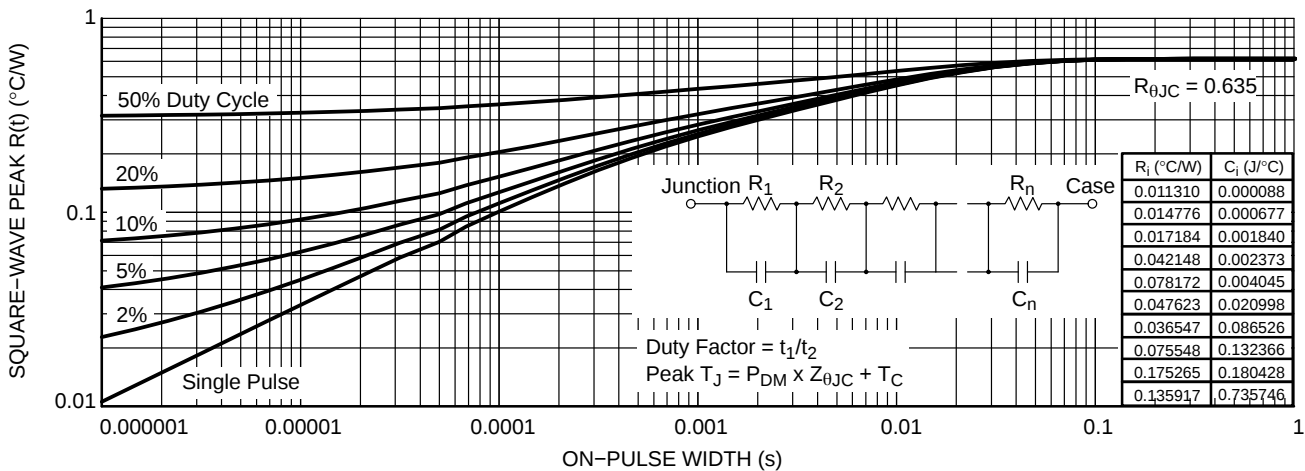
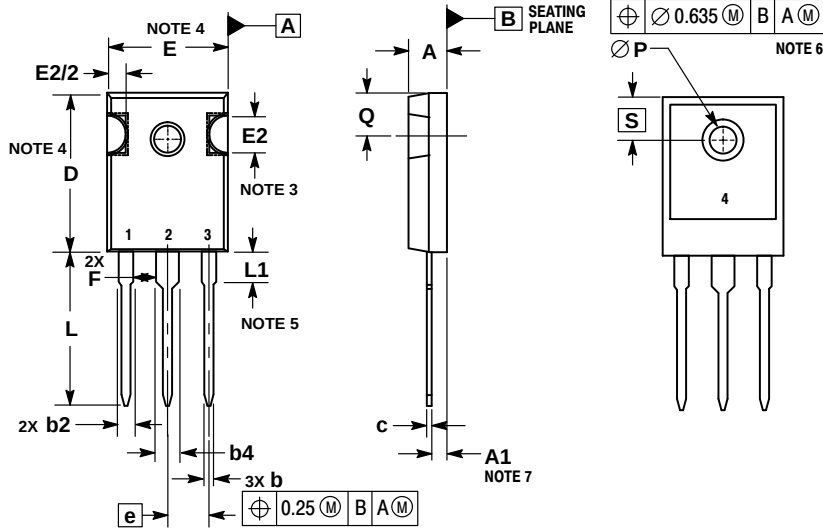


Figure 10. Diode Die Self-heating Square-wave Duty Cycle Transient Thermal Response

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PACKAGE DIMENSIONS

TO-247 CASE 340AL ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. $\varnothing P$ SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS	
	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.00	1.40
b2	1.65	2.35
b4	2.60	3.40
c	0.40	0.80
D	20.80	21.34
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
F	2.655	---
L	19.80	20.80
L1	3.81	4.32
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

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